NPN Triple Diffused Planar Silicon Transistor



2SC4219

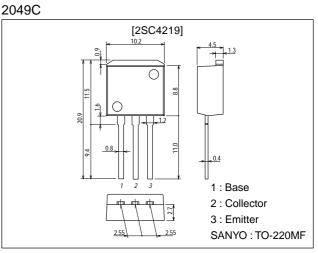
# 400V/4A Switching Regulator Applications

### Features

- $\cdot$  High breakdown voltage, high reliability (V<sub>CEO</sub> $\geq$ 400V).
- · Fast switching speed ( $t_f=0.1\mu s$  typ).
- · Wide ASO.
- · Adoption of MBIT process.
- · Suitable for sets whose height is restricted.

## Package Dimensions

unit:mm



# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		500	V
Collector-to-Emitter Voltage	VCEO		400	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	۱ <sub>C</sub>		4	Α
Collector Current (Pulse)	ICP	PW≤300µs, duty cycle≤10%	8	Α
Base Current	Ι <sub>Β</sub>		1.5	Α
Collector Dissipation	PC		1.65	W
		Tc=25°C	40	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =400V, I <sub>E</sub> =0			10	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB}=5V, I_{C}=0$			10	μΑ
DC Current Gain	*hFE1	$V_{CE}=5V, I_{C}=0.4A$	15		50	
	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =2A	10			
	h <sub>FE</sub> 3	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	10			

\*: The  $h_{FE}1$  of the 2SC4219 is classified as follows. When specifying the  $h_{FE}1$  rank, specify two ranks or more in principle.

15 L 30 20 M 40 30 N 50

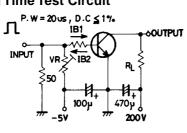
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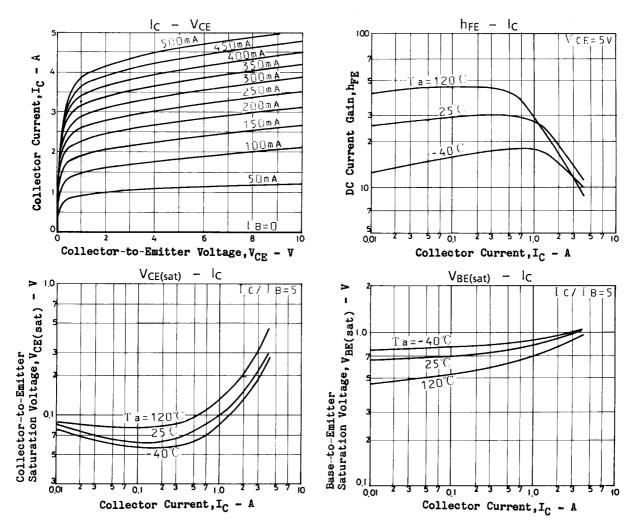
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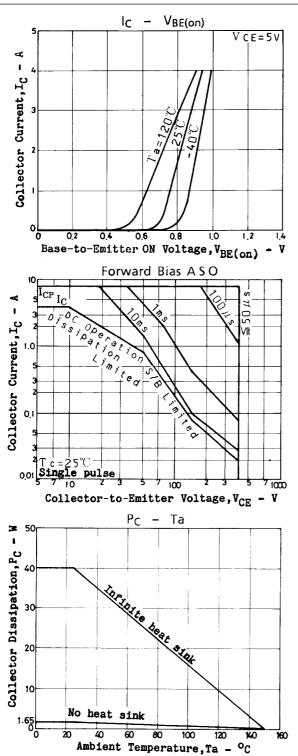
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2A, I <sub>B</sub> =0.4A			0.8	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =2A, I <sub>B</sub> =0.4A			1.5	V
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =0.4A		20		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		50		pF
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =1mA, I <sub>E</sub> =0	500			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =5mA, R <sub>BE</sub> =∞	400			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	7			V
Collector-to-Emitter Sustain Voltage	VCEX(sus)	I <sub>C</sub> =2A, I <sub>B1</sub> =0.2A, L=1mH, I <sub>B2</sub> =-0.8A, clamped	400			V
Turn-ON Time	ton	$I_{C}{=}3A,I_{B1}{=}0.6A,I_{B2}{=}{-}1.2A,R_{L}{=}66.6\Omega,$ $V_{CC}{=}200V$			0.5	μs
Storage Time	t <sub>stg</sub>	$I_{C}=3A$ , $I_{B1}=0.6A$ , $I_{B2}=-1.2A$ , $R_{L}=66.6\Omega$ , $V_{CC}=200V$			2.5	μs
Fall Time	t <sub>f</sub>	$I_{C}$ =3A, $I_{B1}$ =0.6A, $I_{B2}$ =-1.2A, $R_{L}$ =66.6 $\Omega$ , $V_{CC}$ =200V			0.3	μs

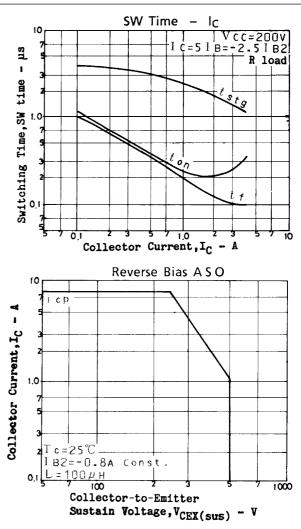
### **Switching Time Test Circuit**



Unit (resistance:  $\Omega$ , capacitance: F)







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